

# James R Shealy

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/12042008/publications.pdf>

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9  
papers

125  
citations

1683934  
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1872570  
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g-index

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all docs

9  
docs citations

9  
times ranked

116  
citing authors

#	ARTICLE	IF	CITATIONS
1	Influence of Field Plate on the Transient Operation of the AlGaIn/GaN HEMT. IEEE Electron Device Letters, 2009, 30, 436-438.	2.2	65
2	Preparation and Properties of Zinc Oxide Films Grown by the Oxidation of Diethylzinc. Journal of the Electrochemical Society, 1981, 128, 558-561.	1.3	20
3	Growth of direct bandgap GaInP quantum dots on GaP substrates. Journal of Electronic Materials, 1997, 26, 1199-1204.	1.0	16
4	Methodology for Small-Signal Model Extraction of AlGaIn HEMTs. IEEE Transactions on Electron Devices, 2008, 55, 1603-1613.	1.6	16
5	Performance of AlGaIn/GaN High-Electron Mobility Transistors With AlSiN Passivation. IEEE Transactions on Electron Devices, 2011, 58, 87-94.	1.6	6
6	Direct Bandgap Quantum Wells on GaP. Materials Research Society Symposia Proceedings, 1996, 448, 165.	0.1	2
7	The Use of Ultraviolet Radiation at the Congruent Sublimation Temperature of Indium Phosphide to Produce Enhanced InP Schottky Barriers. Journal of the Electrochemical Society, 1992, 139, 2961-2968.	1.3	0
8	Al <sub>x</sub> Si <sub>y</sub> N <sub>z</sub> passivated AlGaIn/GaN high electron mobility transistors. , 2009, , .		0
9	440 V AlSiN-passivated AlGaIn/GaN high electron mobility transistor with 40 GHz bandwidth. , 2012, , .		0